

- IR Single Mode Laser Diode 852nm



- **Specifications**

Operating Parameters	Symbol	Min	Typ	Max	Unit
Optical output power	P _{out}	-	100	-	mW
Wavelength	λ	847	852	857	nm
Spectrum	FWHM $\Delta\lambda$	-	0.5	2.0	nm
Threshold current	I _{th}	-	20	40	mA
Forward current	I _f	-	120	170	mA
Forward voltage	V _f	-	1.9	2.2	V
Slope efficiency	$\Delta P/\Delta I$	0.9	1.0	-	W/A
Vertical far field	$\Theta_{ }$	-	18	23	°
Parallel far field	Θ_{\perp}	-	8	10	°

- **Additional information:**

wavelength drift under temperature change - $<0,3\text{nm}/^{\circ}\text{C}$;

LD reverse voltage - 2V;

PD reverse voltage - 30V;

Operating temperature - -20°C + 50°C ;

Storage temperature - -40°C + 80°C

Lifetime - >100000 hours

Lead soldering temperature - 250°C for 5sec

- **Additional information:**

C2 chip on 2.1mm sub mount

M9 9mm TO-can with or without PD